

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
30V	$73\text{m}\Omega$ @ $V_{GS} = 10\text{V}$	3.3A
	$110\text{m}\Omega$ @ $V_{GS} = 4.5\text{V}$	2.7A

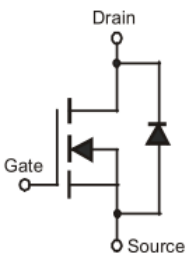
Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

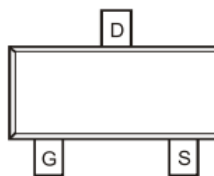
- General Purpose Interfacing Switch
- Power Management Functions
- Boost Application
- Analog Switch



TOP VIEW



Internal Schematic



TOP VIEW

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

Mechanical Data

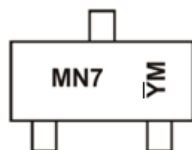
- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.027 grams (approximate)

Ordering Information (Note 4)

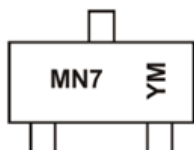
Part Number	Case	Packaging
DMN3110S-7	SOT-23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



Chengdu A/T Site



Shanghai A/T Site

MN7 = Product Type Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)
 Y or Y̅ = Year (ex: A = 2013)
 M = Month (ex: 9 = September)

Date Code Key

Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	2.5	A
		T _A = +70°C		2.0	
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	3.3	A
		T _A = +70°C		2.7	
Continuous Drain Current (Note 6) V _{GS} = 10V	t ≤ 10sec	T _A = +25°C	I _D	3.8	A
		T _A = +70°C		3.1	
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	2.7	A
		T _A = +70°C		2.1	
Pulsed Drain Current (Note 7)			I _{DM}	25	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	0.74	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	173.4	°C/W
Total Power Dissipation (Note 6)	P _D	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	99.1	°C/W
Total Power Dissipation (Note 6) t ≤ 10sec	P _D	1.8	W
Thermal Resistance, Junction to Ambient (Note 6) t ≤ 10sec	R _{θJA}	72	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current @T _C = +25°C	I _{DSS}	-	-	1.0	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.0	-	3.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	54	73	mΩ	V _{GS} = 10V, I _D = 3.1A
		-	88	110		V _{GS} = 4.5V, I _D = 2A
Forward Transfer Admittance	Y _{fs}	-	4.8	-	mS	V _{DS} = 10V, I _D = 3.1A
Diode Forward Voltage (Note 6)	V _{SD}	-	0.75	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	-	305.8	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	39.9	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	39.5	-	pF	
Gate Resistance	R _g	-	1.4	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	-	4.1	-	nC	V _{GS} = 10V, V _{DS} = 10V, I _D = 3A
Total Gate Charge (V _{GS} = 10V)	Q _g	-	8.6	-	nC	
Gate-Source Charge	Q _{gs}	-	1.2	-	nC	
Gate-Drain Charge	Q _{gd}	-	1.5	-	nC	V _{DD} = 15V, V _{GS} = 10V, R _L = 47Ω, R _G = 3Ω,
Turn-On Delay Time	t _{D(on)}	-	2.6	-	ns	
Turn-On Rise Time	t _r	-	4.6	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	13.1	-	ns	
Turn-Off Fall Time	t _f	-	2.5	-	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, on 1inch square copper plate
 - Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

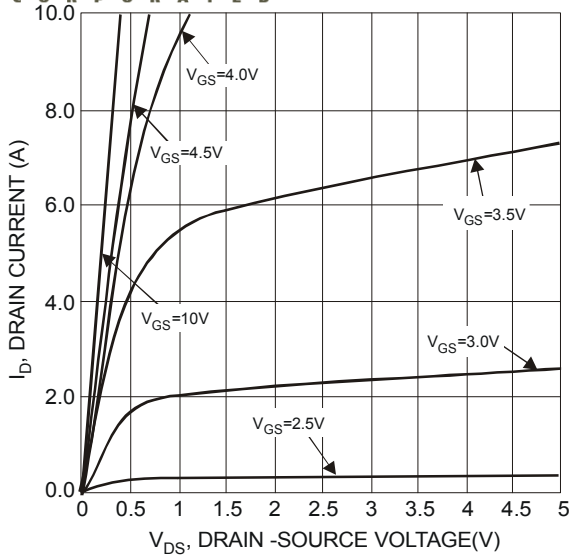


Fig. 1 Typical Output Characteristics

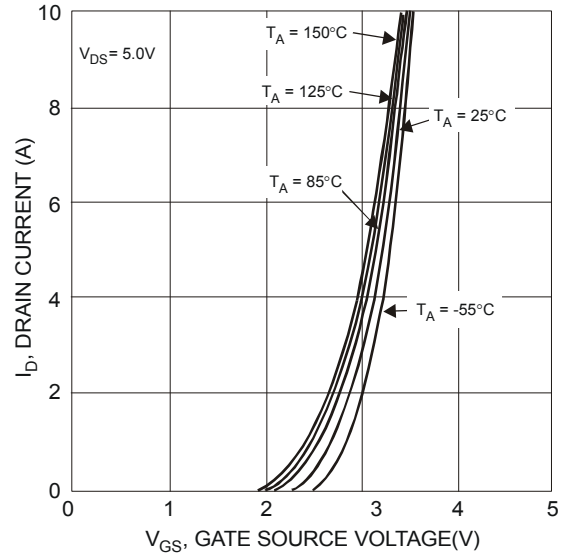


Fig. 2 Typical Transfer Characteristics

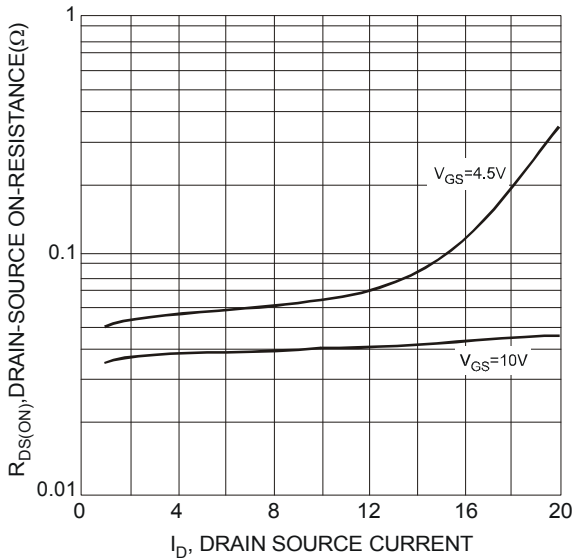


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

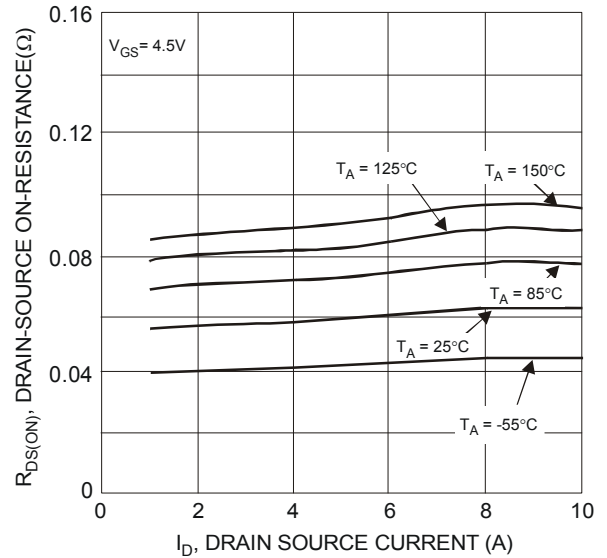


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

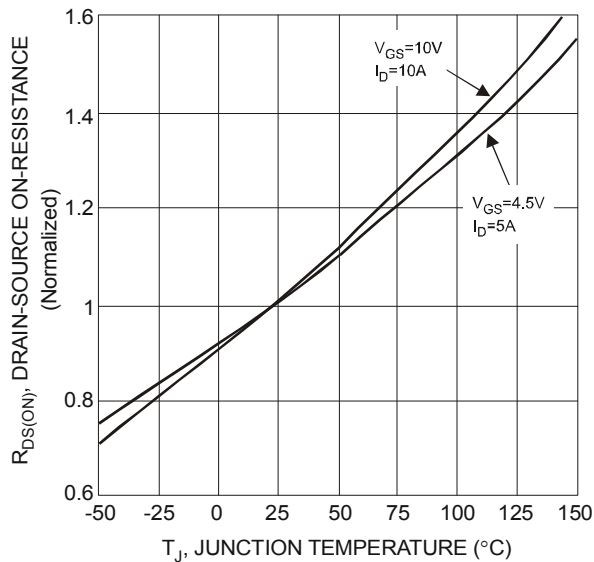


Fig. 5 On-Resistance Variation with Temperature

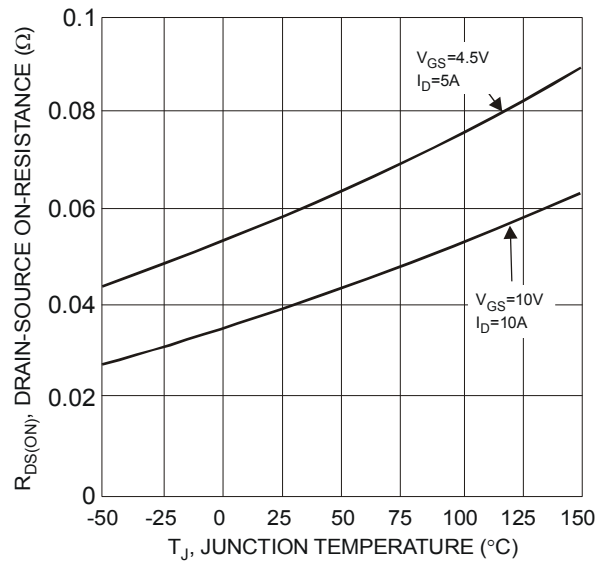


Fig. 6 On-Resistance Variation with Temperature

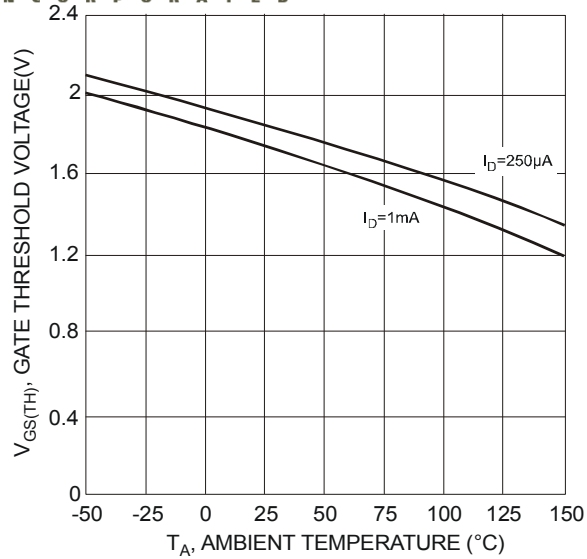


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

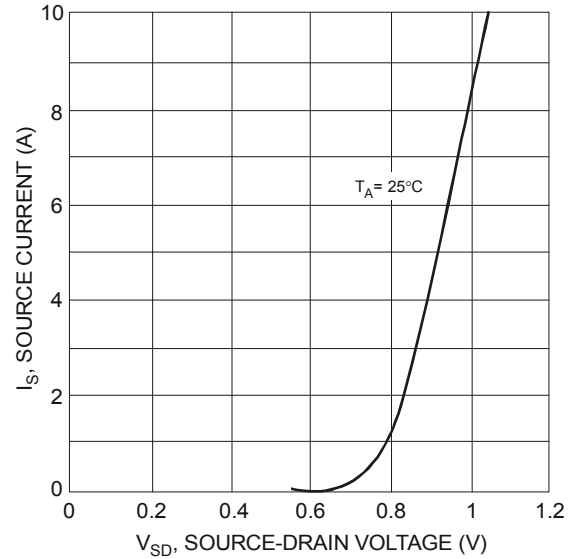


Fig. 8 Diode Forward Voltage vs. Current

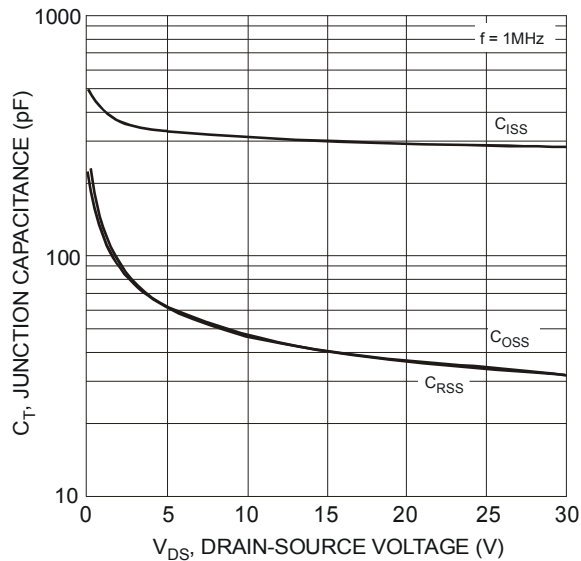


Fig. 9 Typical Junction Capacitance

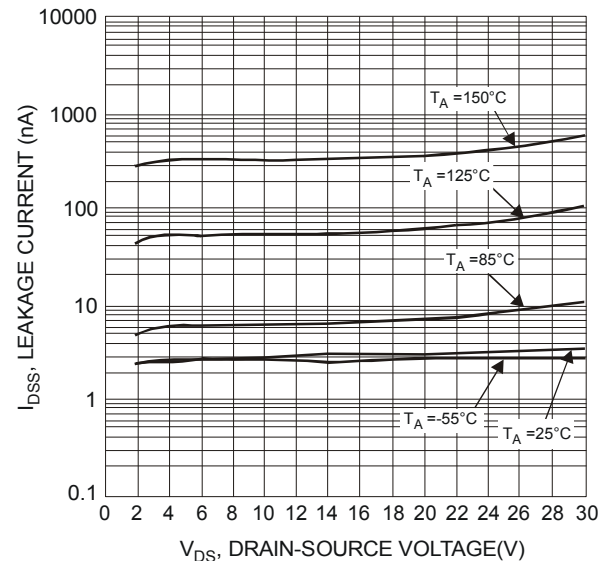


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

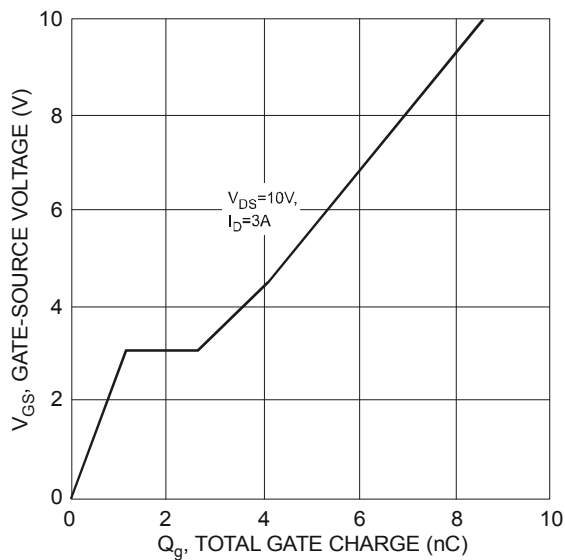
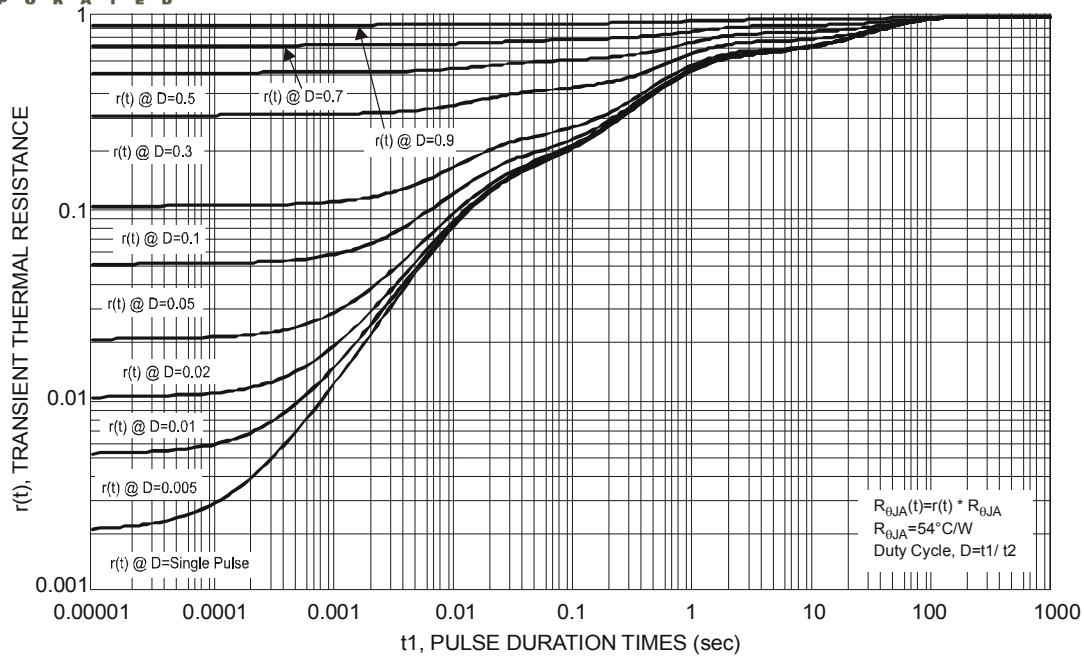
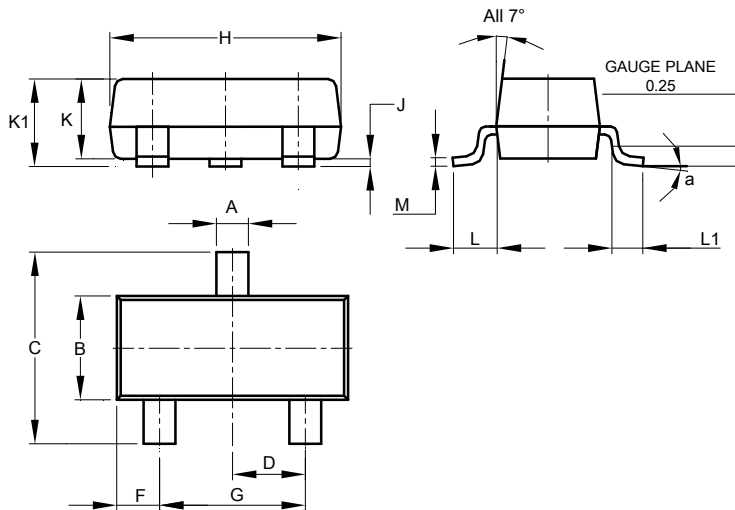


Fig. 11 Gate-Charge Characteristics



Package Outline Dimensions

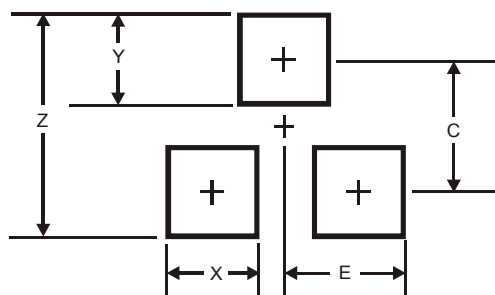
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
α	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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